

1. Scope :

This specification applies to silicon zerocrossing phototriac chips,
Device No. ST-0172S

2. Structure :

- 2-1. Planar type .
- 2-2. Electrodes :aluminum alloy

3. Size :

- 3-1. Chip size : 40.0 mils × 40.0 mils (1.016 mm ×1.016mm).
- 3-2. Chip thickness : 12±1.0 mil (0.305± 0.025 mm).
- 3-3. Pad area : 5.4 mil dia (0.137 mm).
- 3-4. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

パラメーター Parameter	記号 Symbol	条件 Condition	最小 値 Min.	代表 値 Typ.	最大 値 Max.	単位 Unit	テス ト Test
せん頭オフ電流 Peak off-state Current	I_{DRM}	$V_{DRM}=860V$			500	nA	100%
せん頭オン電圧 Peak on-state voltage	V_{TM}	$I_{TM}=100mA$		1.6	2.0	V	100%
トリガ電流 Trigger current	I_{GT}	$V_T=6V$	2	5	10	uA	100%
G K間抵抗 Resistance between G and K	R_{GK}	$V_{GK}=0.2V$	100	130	160	kΩ	100%
pnp電流増幅率 *1 pnp current gain	α_{pnp} (= $-I_C/I_E$)	$V_{CB}=-3V$ $I_E=50\mu A$	0.090	0.120	0.150	-	1%
nnp電流増幅率 *1 nnp current gain	β_{nnp} (= I_C/I_B)	$V_{CE}=3V$ $I_B=50\mu A$	15	22	30	-	1%
オフ電圧上昇率 *2 Critical rate of Rise voltage	dv/dt		1000			V/us	

